

**isc Silicon PNP Power Transistor**
**MJE2955T**
**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -60V(\text{Min})$
- High DC Current Gain-  
:  $h_{FE} = 20-100 @ I_C = -4A$
- Complement to Type MJE3055T
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

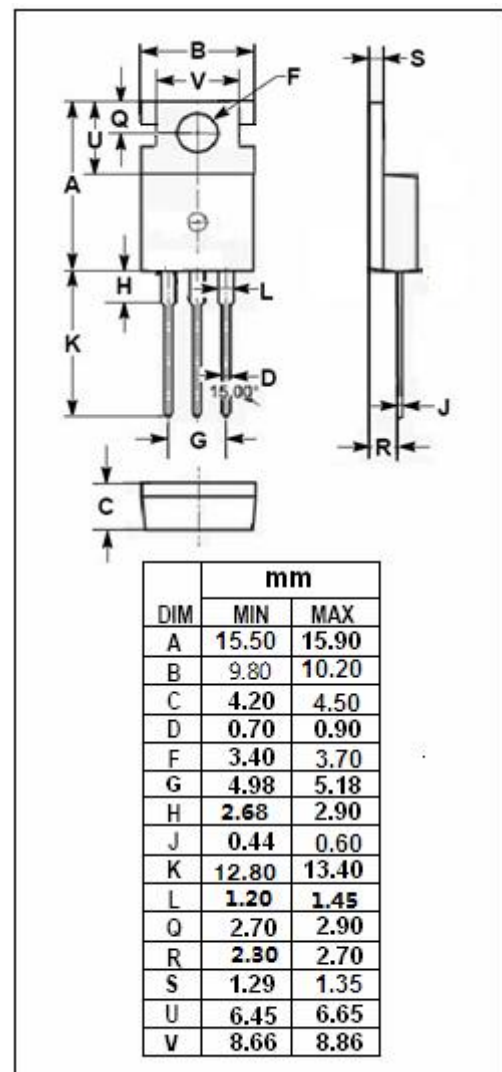
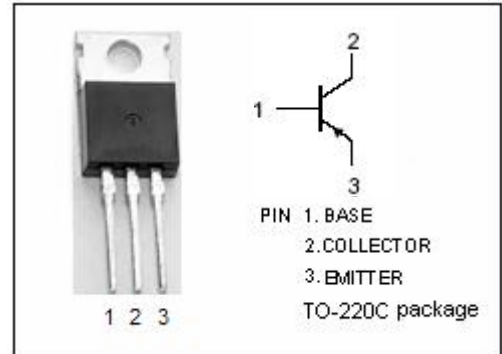
- Designed for use in general-purpose amplifier and switching applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-70	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-10	A
$I_B$	Base Current-Continuous	-6	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	75	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ\text{C/W}$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = 0	-60			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A			-1.1	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10A; I <sub>B</sub> = -3.3A			-8.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -4A; V <sub>CE</sub> = -4V			-1.8	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -30V; I <sub>B</sub> = 0			-0.7	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -70V; I <sub>E</sub> = 0 V <sub>CB</sub> = -70V; I <sub>E</sub> = 0; T <sub>C</sub> = 150°C			-1.0 -10	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-5.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -4V	20		100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -10A; V <sub>CE</sub> = -4V	5			
f <sub>T</sub>	Current Gain-Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V; f= 500kHz	2.0			MHz

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